# P-Channel 20-V (D-S) MOSFET

### **Key Features:**

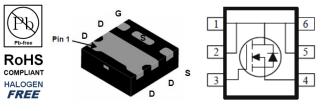
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- Fast switching speed

### **Typical Applications:**

- Load Switches
- DC/DC Conversion
- Motor Drives

PRODUCT SUMMARY				
Vds (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
-20	56 @ V <sub>GS</sub> = -4.5V	-5.0		
	80 @ V <sub>GS</sub> = -2.5V	-4.2		
	130 @ V <sub>GS</sub> = -1.8V	-3.3		





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)							
Parameter				Limit	Units		
Drain-Source Voltage				-20	V		
Sate-Source Voltage				±8	V		
Continuous Drain Current <sup>a</sup>		T <sub>A</sub> =25°C	1	-5.0			
Continuous Drain Current		T <sub>A</sub> =70°C	ID	-4.5	А		
ulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-20				
Continuous Source Current (Diode Conduction) <sup>a</sup>			۱ <sub>s</sub>	-2.5	А		
Device Discipation <sup>a</sup>		T <sub>A</sub> =25°C	P <sub>D</sub>	2.1	w		
Power Dissipation <sup>a</sup>	Τ <sub>Α</sub>		۰D	1.7	vv		
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	R <sub>eja</sub>	62.5	°C/W			
	Steady State	ιν <sub>θ</sub> ja	110	C/vv			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Мах	Unit		
Static								
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.4			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			±100	nA		
Zero Gate Voltage Drain Current		$V_{DS} = -16 V, V_{GS} = 0 V$			-1 uA			
	I <sub>DSS</sub>	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	C -10		uл			
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 V, V_{GS} = -4.5 V$	-7.5			Α		
		$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -4 \text{ A}$			56			
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS}$ = -2.5 V, $I_{D}$ = -3.2 A			80	mΩ		
		$V_{GS}$ = -1.8 V, $I_{D}$ = -2.6 A			130			
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -4 \text{ A}$		10		S		
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = -1.3 \text{ A}, V_{GS} = 0 \text{ V}$		-0.77		V		
		Dynamic <sup>b</sup>						
Total Gate Charge	Qg	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = -4.5 V,		12				
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -10$ V, $V_{GS} = -4.3$ V, $I_{D} = -2$ A		1.7		nC		
Gate-Drain Charge	Q <sub>gd</sub>			2.6				
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = -10 V, R <sub>L</sub> = 5 Ω,		10				
Rise Time	t <sub>r</sub>	$v_{DS} = -10 v$ , $R_L = -3 \Omega_2$ , $I_D = -2 A$ .		13		ns		
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN} = -4.5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		50				
Fall Time	t <sub>f</sub>	$v_{\text{GEN}} = \pm .0$ $v_{1}$ $r_{\text{GEN}} = 0.22$		20				
Input Capacitance	C <sub>iss</sub>			694				
Output Capacitance	C <sub>oss</sub> C <sub>rss</sub>	$V_{DS} = -15 V, V_{GS} = 0 V, f = 1 Mhz$		82		pF		
Reverse Transfer Capacitance				63				

#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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1

0.6

5

10

6. Capacitance

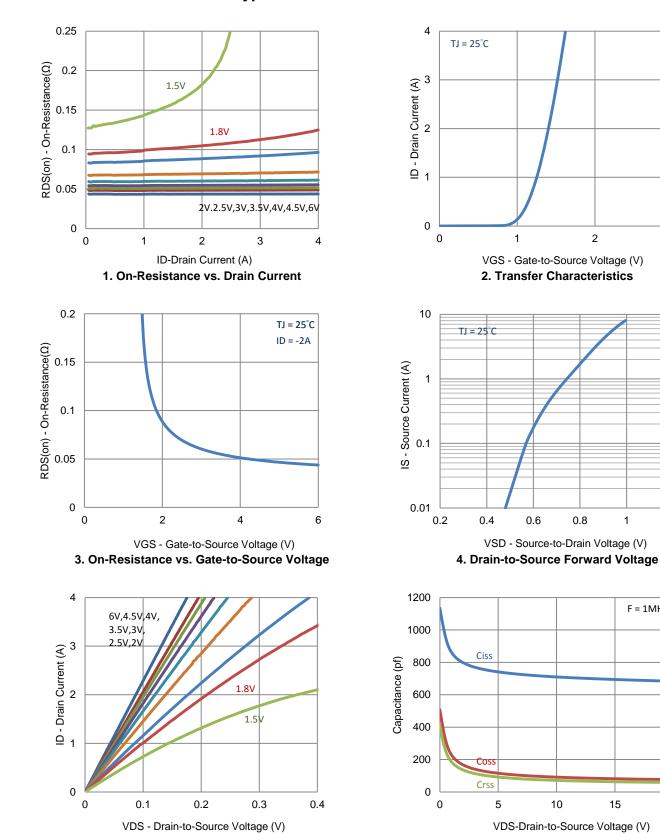
0.8

1

F = 1MHz

1.2

2

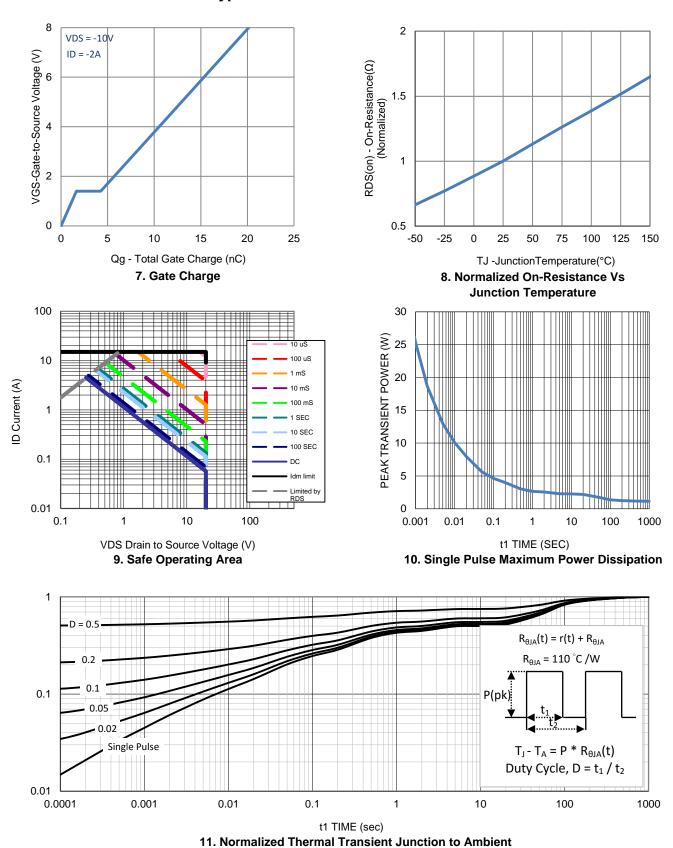


### **Typical Electrical Characteristics**

5. Output Characteristics

15

20



### **Typical Electrical Characteristics**

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1

2e

<u>Bottom view</u>

D2

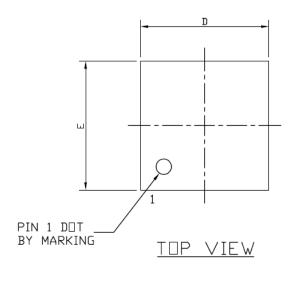
D1

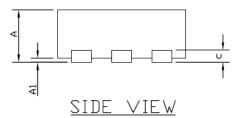
e

b

-1

## Package Information





SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
STMBULS	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.50	0.55	0.60	0.020	0.022	0.024	
A1	0.00		0.05	0.000		0.002	
b	0.25	0.25	0.28	0.009	0.010	0.011	
с	0.152 Ref.			0.006 Ref.			
D	1.55	1.60	1.65	0.061	0.063	0.065	
D1	0.67 TYP			0.026 TYP			
D2	0.75 TYP				0.030 TY	P	
E	1.55	1.60	1.65	0.061	0.063	0.065	
E1	0.98 TYP			0.039 TYP			
e	0.50 BSC			0.020 BSC			
L	0.20	0.25	0.30	0.008	0.010	0.012	